

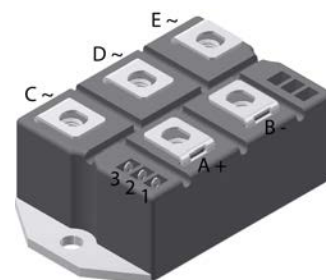
Thyristor Module

3~ Rectifier
$V_{RRM} = 1200\text{ V}$
$I_{DAV} = 170\text{ A}$
$I_{FSM} = 1500\text{ A}$

3~ Rectifier Bridge, half-controlled (high-side)

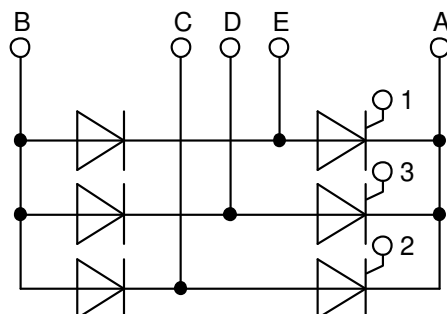
Part number

VVZ175-12io7



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Line rectifying 50/60 Hz
- Drives
- SMPS
- UPS

Package: PWS-E

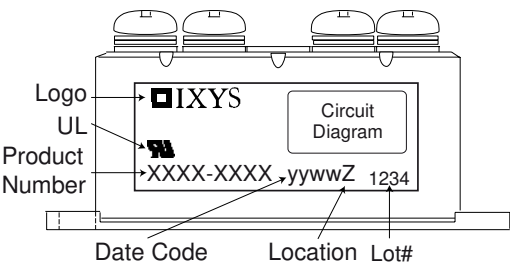
- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			300	μA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			5	mA
V_T	forward voltage drop	$I_T = 60\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,09	V
		$I_T = 180\text{ A}$				1,42	V
		$I_T = 60\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,03	V
		$I_T = 180\text{ A}$				1,44	V
I_{DAV}	bridge output current	$T_C = 85^{\circ}\text{C}$ rectangular $d = 1/3$	$T_{VJ} = 125^{\circ}\text{C}$			170	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}\text{C}$			0,82	V
r_T	slope resistance					3,5	m Ω
R_{thJC}	thermal resistance junction to case					0,46	K/W
R_{thCH}	thermal resistance case to heatsink				0,09		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			220	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1,50	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1,62	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			1,28	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1,38	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			11,3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			10,9	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			8,13	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			7,87	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		95		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 125^{\circ}\text{C}$			10	W
		$t_p = 300\text{ }\mu\text{s}$				1	W
P_{GAV}	average gate power dissipation					0,5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 180\text{ A}$				150	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0,3\text{ A}/\mu\text{s};$ $I_G = 0,3\text{ A}; V_D = 2/3 V_{DRM}$ non-repet., $I_T = 60\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}\text{C}$			1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1,5	V
			$T_{VJ} = -40^{\circ}\text{C}$			1,6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = 2/3 V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			0,2	V
I_{GD}	gate non-trigger current					5	mA
I_L	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			450	mA
		$I_G = 0,3\text{ A}; di_G/dt = 0,3\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
t_{gd}	gate controlled delay time	$V_D = 1/2 V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0,3\text{ A}; di_G/dt = 0,3\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 60\text{ A}; V_D = 2/3 V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 20\text{ V}/\mu\text{s}; t_p = 300\text{ }\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$		200		μs

Package PWS-E				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	<i>RMS current</i>	per terminal				250	A
T _{VJ}	<i>virtual junction temperature</i>			-40		125	°C
T _{op}	<i>operation temperature</i>			-40		100	°C
T _{stg}	<i>storage temperature</i>			-40		125	°C
Weight					284		g
M _D	<i>mounting torque</i>			4,25		5,75	Nm
M _T	<i>terminal torque</i>			4,25		5,75	Nm
d _{Spp/App}	<i>creepage distance on surface striking distance through air</i>	<i>terminal to terminal</i>		12,0			mm
d _{Spb/Apb}		<i>terminal to backside</i>		26,0			mm
V _{ISOL}	<i>isolation voltage</i>	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V

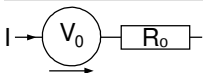


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VVZ175-12io7	VVZ175-12io7	Box	5	464937

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}\text{C}$



Thyristor

$V_{0\text{ max}}$

threshold voltage

0,82

V

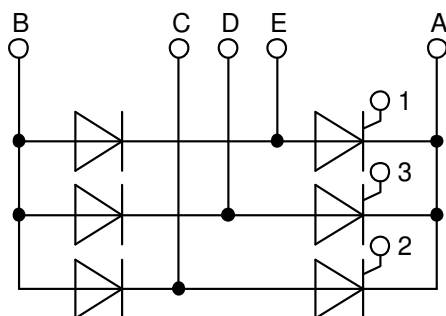
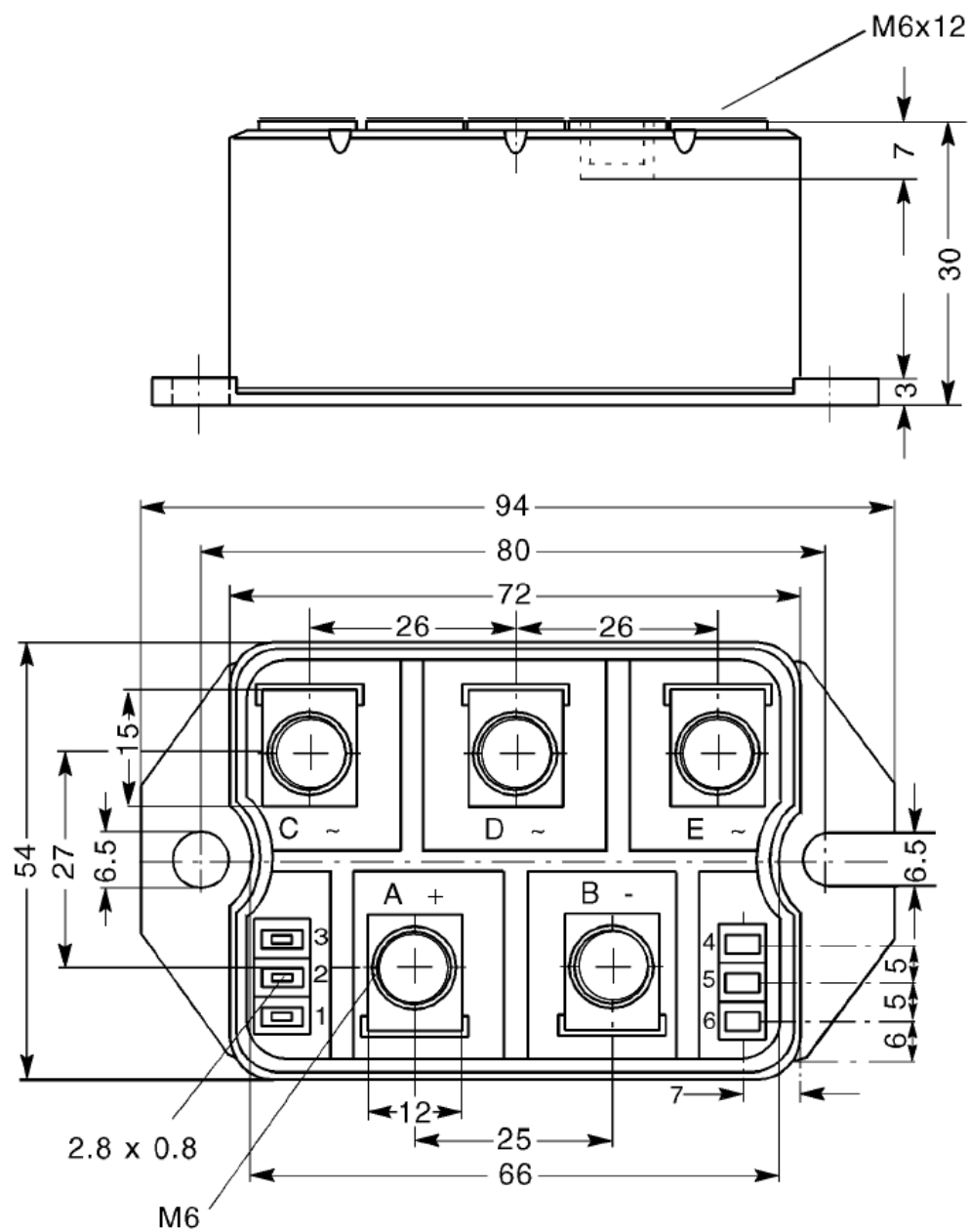
$R_{0\text{ max}}$

*slope resistance **

2,3

mΩ

Outlines PWS-E



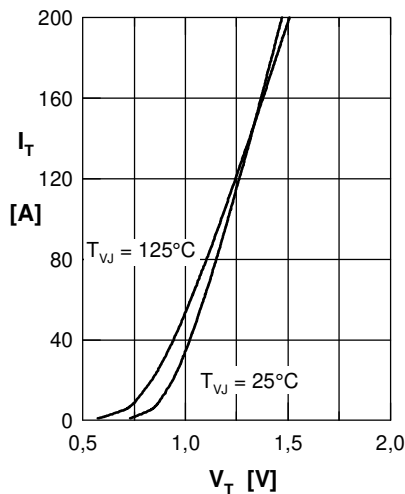
Thyristor


Fig. 1 Forward characteristics

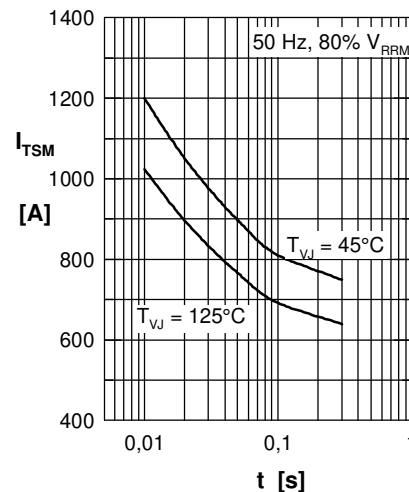
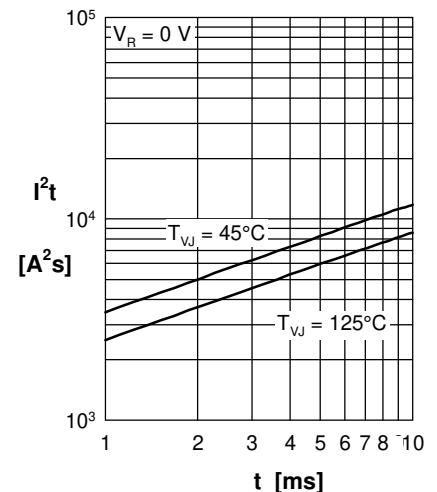
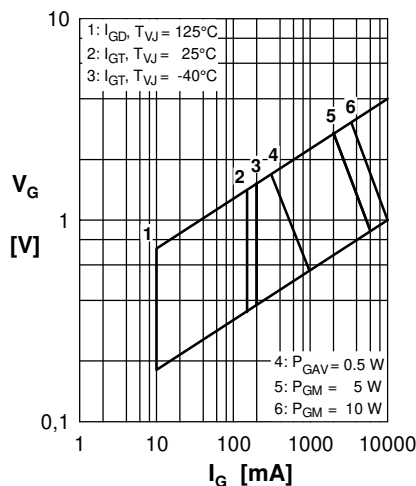

 Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

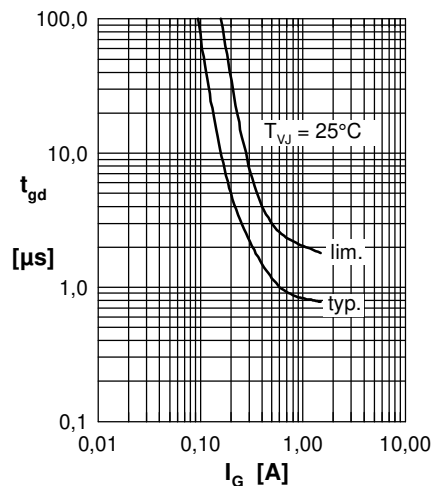
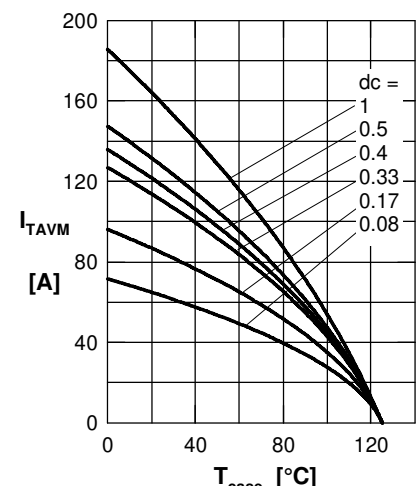

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

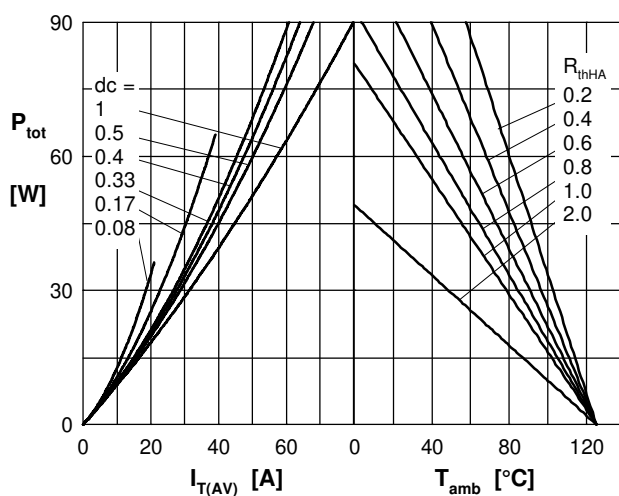
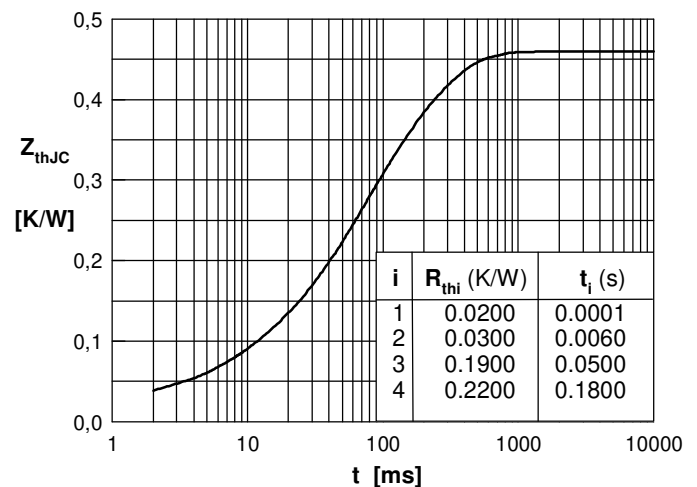

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case